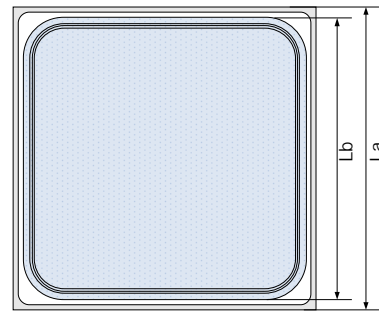


**2SB065020MTJY SCHOTTKY BARRIER DIODE CHIPS**
**DESCRIPTION**

- Ø 2SB065020MTJY is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø Low forward voltage drop;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size:650μm X 650μm;
- Ø Chip Thickness: 155±20um
- Ø Gross die:26000 Die/Wafer(5 inch)


**Chip Topography and Dimensions**

La: Chip Size: 650μm;

Lb: Pad Size: 580μm;

**ORDERING SPECIFICATIONS**

Product Name	Specification
2SB065020MTJY	For Au and AlSi wire bonding package

**ABSOLUTE MAXIMUM RATINGS**

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	20	V
Average Forward Rectified Current	IFAV	0.5	A
Peak Forward Surge Current@8.3ms	IFSM	5.5	A
Maximum Operation Junction Temperature	TJ	125	°C
Storage Temperature Range	TSTG	-40~125	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C)**

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=250μA	20	--	V
Forward Voltage	VF1	IF=100mA	--	0.30	V
	VF2	IF=500mA	--	0.385	V
Reverse Current	IR1	VR=10V	--	75	μA
	IR2	VR=20V		250	μA